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a wiring layer formed on the insulation layer,
the electrodes of the semiconductor chip and the wiring layer being connected to each other via connection members disposed in the insulation layer wherein said connection members extend in a direction perpendicular to the semiconductor chip, have a longitudinal shape, and have an area of contact with the wiring layer that is less than an area of contact with an electrode.

7. (Amended) A method for fabricating a semiconductor device comprising the steps of:

preparing a wafer including a plurality of semiconductor chips with electrodes formed thereon;

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forming connection members on the electrodes of the respective semiconductor chips, the connection members extending in a direction perpendicular to the semiconductor chips and having a longitudinal shape and an area of contact with a herein later identified wiring layer that is less than an area of contact with an electrode;

forming an insulation layer in a thickness to cover the connection members on the surfaces of the respective semiconductor chips where the electrodes of the semiconductor chips are formed;

polishing the insulation layer to expose the connection members;

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forming an electroless plated layer on the insulation layer; and
forming, with the electroless plated layer as a feeder layer of electric current, an electrolytic plated layer on the electroless plated layer selectively only in regions for a wiring layer;

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cont. etching off the electroless plated layer except regions of the electroless plated layer corresponding to the electrolytic plated layer to form the wiring layer including the electroless plated layer and the electrolytic plated layer; and

severing the wafer into the respective semiconductor chips to fabricate the semiconductor device.

Please add the following new claims:

16. (New) The semiconductor device according to claim 2, wherein the wire bumps are Au wire bumps.

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17. (New) The method for fabricating a semiconductor device according to claim 9, wherein the wire bumps are Au wire bumps.
